

# 838um×838um Silicon PD Chip datasheet

**P/N : WS9K-10B**

## Application

Si NIP photodiode chips

## Structure

Planar type : NIP diode

Electrodes :

Top side ( Cathode ) : Al

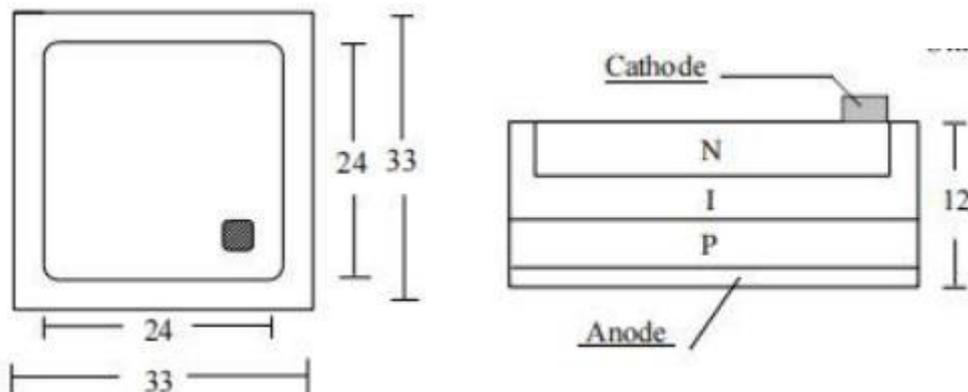
Backside ( Anode ) : Au Alloy

## DIMENSIONS

Conditions	Min.	Typ.	Max.	Unit
Active	24 × 24 ( ± 1.0 )			mil
Chip width	33 × 33 ( ± 1.5 )			mil
Chip length	33 × 33 ( ± 1.5 )			mil
Chip height	12 ± ( 1.0 )			mil
Pad N( Cathode )	5.6 × 5.6			mil
Pad P(Anode )	5.6 × 5.6			mil

## Electro-Optical Characteristics ( @ Ta=25 °C)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward Voltage	VF	IF=10mA, H=0	0.5		1.3	V
Reverse Voltage	VBR	IR=100μA, H=0	35			V
Reverse Dark Current	ID	VR=10V, H=0			10	nA
Sensitive Wavelength Range	λp			940		nm
Capacitance	CJ	VR=3V, F=1 MHz		9		pF



Unit : mil